FAIRCHILD™

Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD SEMICONDUCTOR®

March 2011

FDS86140

N-Channel PowerTrench® MOSFET

100 V, 11.2 A, 9.8 mΩ

Features

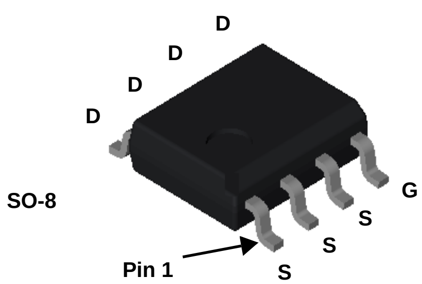
- Max $r_{DS(on)}$ = 9.8 mΩ at V_{GS} = 10 V, I_D = 11.2 A
- Max $r_{DS(on)}$ = 16 mΩ at V_{GS} = 6 V, I_D = 9 A
- High performance trench technologh for extremely low $r_{DS(on)}$
- High power and current handing capability in a widely used surface mount package
- 100% UIL Tested
- RoHS Compliant

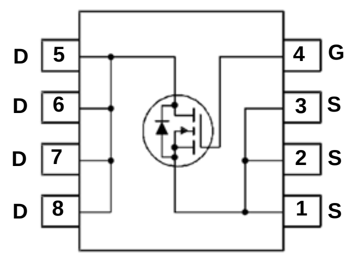
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

Applications

- DC/DC Converters and Off-Line UPS
- Distributed Power Architectures and VRMs
- Primary Swith for 24 V and 48 V Systems
- High Voltage Synchronous Rectifier





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			100	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous			11.2	A
	-Pulsed			50	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	264	mJ
P_D	Power Dissipation	T_C = 25 °C	(Note 1)	5.0	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

Symbol	Parameter		Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS86140	FDS86140	SO-8	13''	12 mm	2500 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		70		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2	2.7	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-11		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 11.2 A		8.1	9.8	mΩ
		V_{GS} = 6 V, I_D = 9 A		10.8	16	
		V_{GS} = 10 V, I_D = 11.2 A, T_J = 125 °C		13.1	17	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 11.2 A		35		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		1940	2580	pF
C_{oss}	Output Capacitance			440	585	pF
C_{rss}	Reverse Transfer Capacitance			20	30	pF
R_g	Gate Resistance			0.9		Ω

Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 11.2 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		13.7	25	ns
t_r	Rise Time			5.6	11	ns
$t_{d(off)}$	Turn-Off Delay Time			23	38	ns
t_f	Fall Time			4.8	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 50 V, I_D = 11.2 A		29	41	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 5 V; V_{DD} = 50 V, I_D = 11.2 A		16.5	23	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 50 V, I_D = 11.2 A		8.0		nC
Q_{gd}	Gate to Drain "Miller" Charge			6.5		nC

Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 11.2 A (Note 2)		0.8	1.3	V
		V_{GS} = 0 V, I_S = 2 A (Note 2)		0.7	1.2	
t_{rr}	Reverse Recovery Time	I_F = 11.2 A, di/dt = 100 A/μs		53	85	ns
Q_{rr}	Reverse Recovery Charge			59	94	nC

NOTES:
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) 50 °C/W when mounted on a 1 in^2 pad of 2 oz copper.

b) 125 °C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25 °C, L = 1 mH, I_{AS} = 23 A, V_{DD} = 90 V, V_{GS} = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

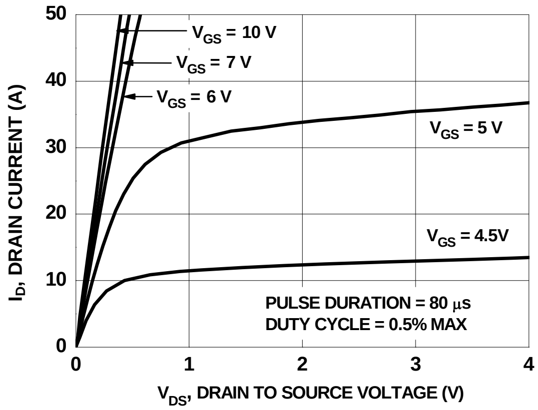


Figure 1. On Region Characteristics

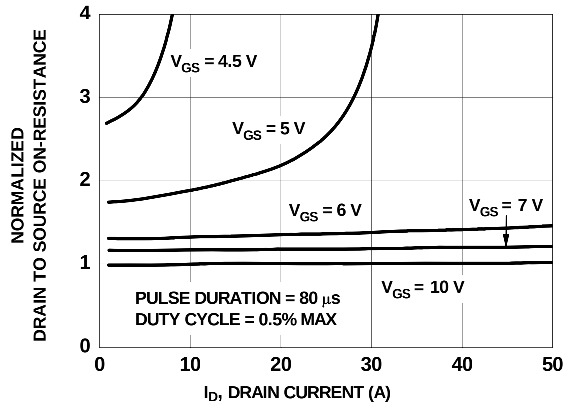


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

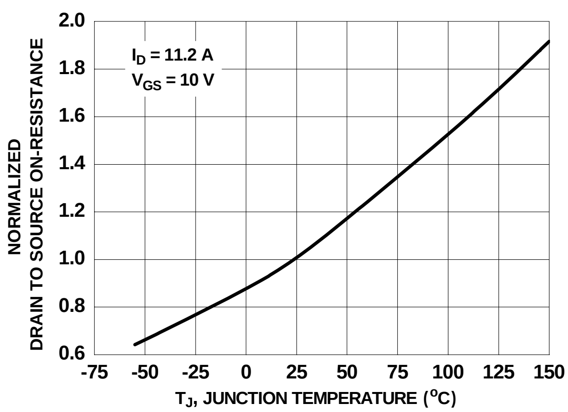


Figure 3. Normalized On Resistance vs Junction Temperature

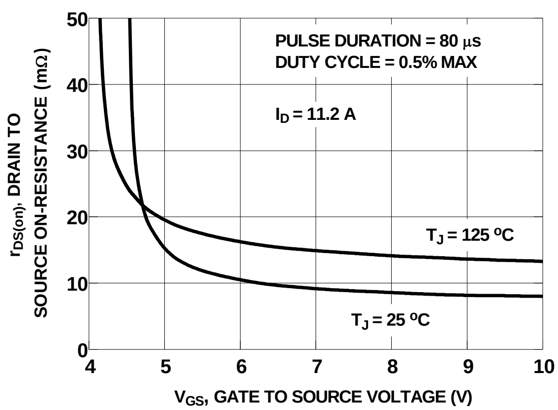


Figure 4. On-Resistance vs Gate to Source Voltage

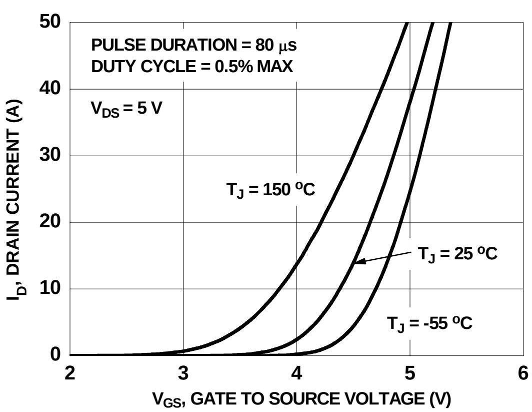


Figure 5. Transfer Characteristics

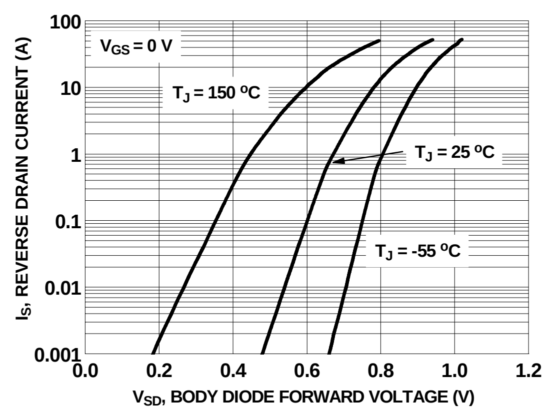


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

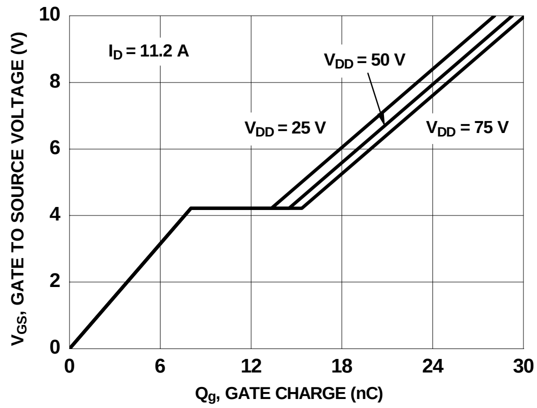


Figure 7. Gate Charge Characteristics

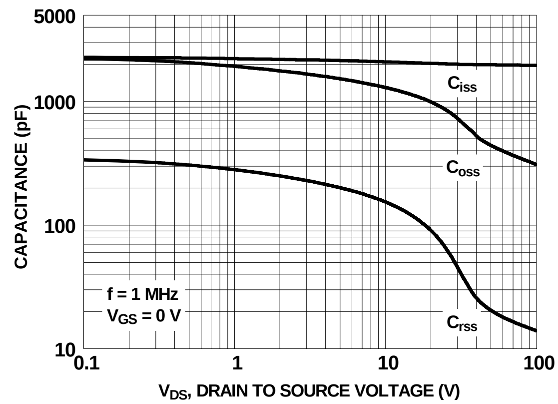


Figure 8. Capacitance vs Drain to Source Voltage

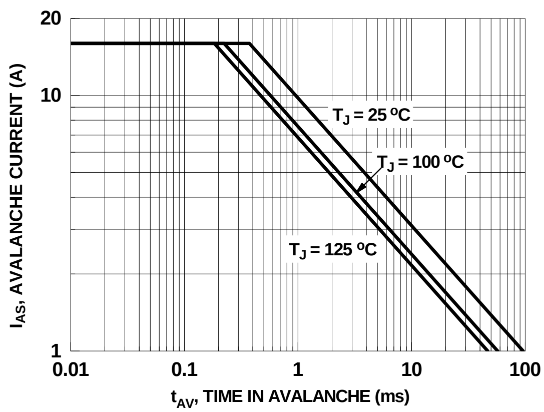


Figure 9. Unclamped Inductive Switching Capability

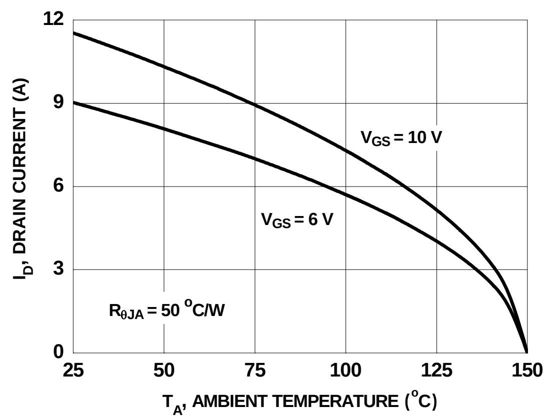


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

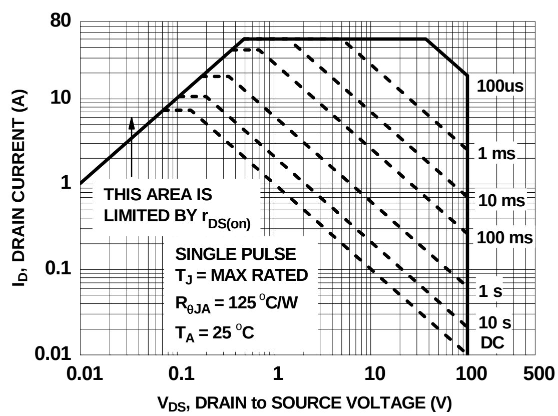


Figure 11. Forward Bias Safe Operating Area

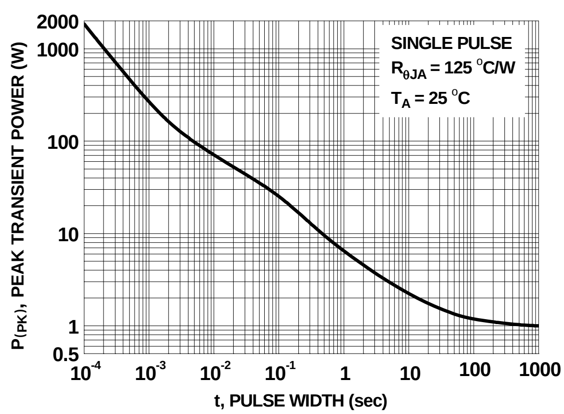


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

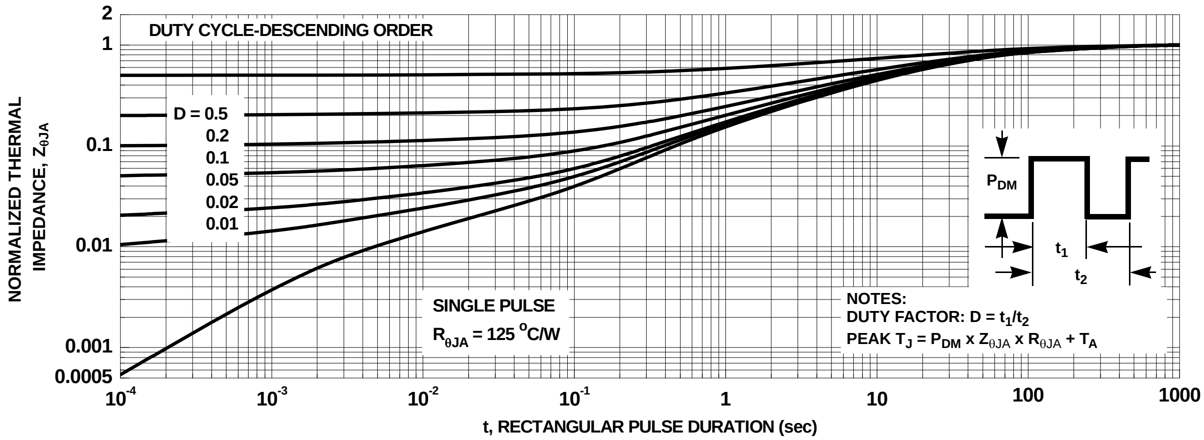
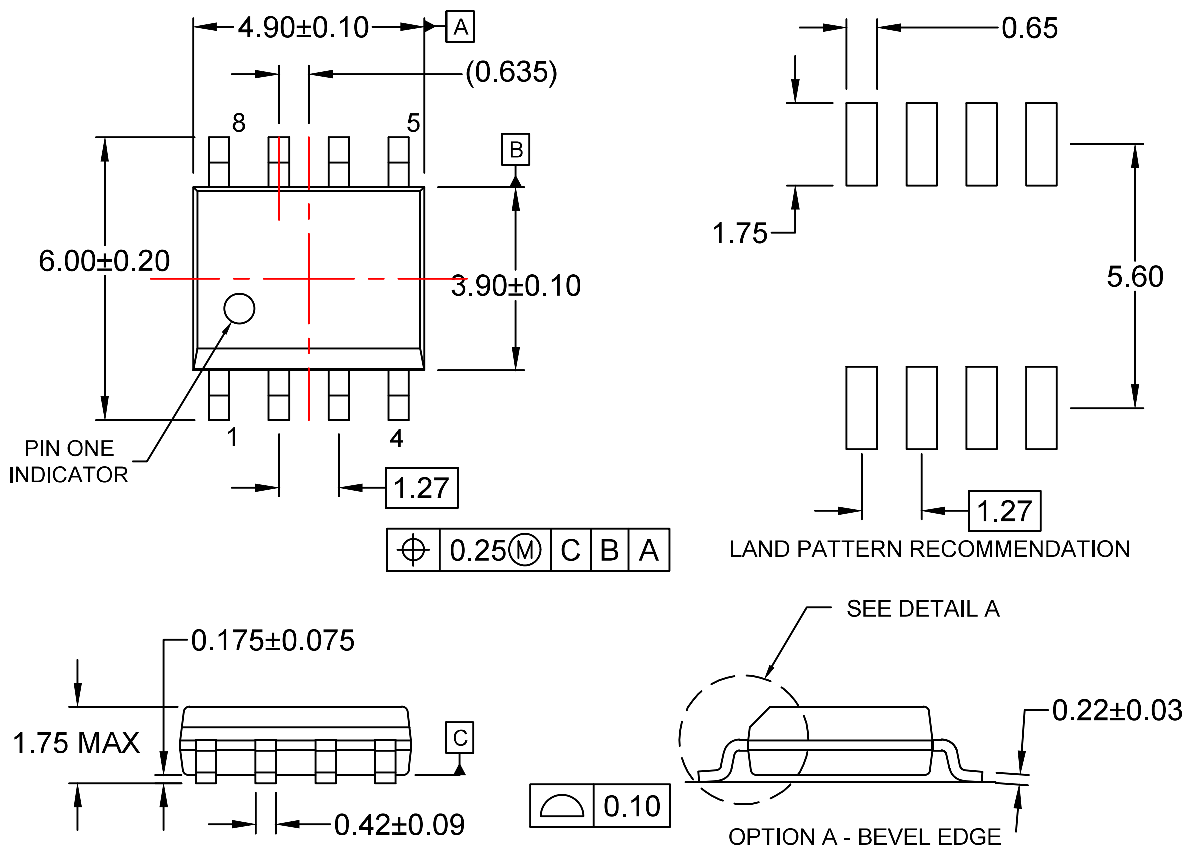
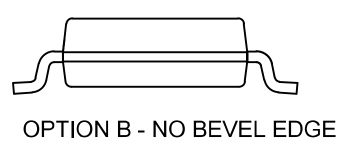
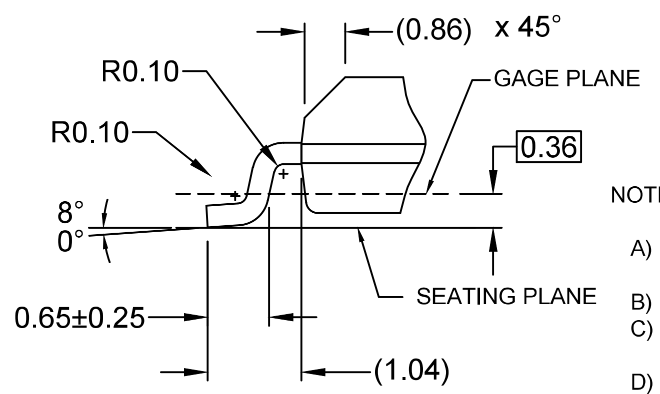


Figure 13. Junction-to-Ambient Transient Thermal Response Curve







DETAIL A
SCALE: 2:1

NOTES:

A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
D) LANDPATTERN STANDARD: SOIC127P600X175-8M
E) DRAWING FILENAME: M08Arev16

FAIRCHILD.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative